

InAsSb photovoltaic detector

P12691-201G

High-speed response and high sensitivity in the 8 µm spectral band Thermoelectrically cooled infrared detector with no liquid nitrogen required

The P12691-201G is an infrared detector that provides high sensitivity in the 8 µm spectral band by employing our unique crystal growth technology, back-illuminated structure and integrating a lens. The InAsSb photovoltaic detector has a PN junction that ensures high-speed response and high reliability. Typical applications include gas analysis such as NO, NO2, SO2, and H2S. The P12691-201G is easy to use as it uses a compact package (TO-8) not requiring liquid nitrogen.

Features

- High-speed response
- → High sensitivity
- High reliability
- Compact, thermoelectrically cooled TO-8 package
- RoHS compliant
- Can be assembled in a module with QCL

Applications

- Gas analysis
- Radiation thermometers
- → Thermal imaging
- Remote sensing
- Spectrophotometers

Options (sold separately)

■ Heatsink for two-stage TE-cooled type A3179-01

■ Temperature controller C1103-04

■ Infrared detector module with preamp C4159-07

Structure

Parameter	Specification	
Window material	Ge with AR coating	-
Package	TO-8	-
Cooling	Two-stage TE cooler	-
Photosensitive area	φ1.0	mm

Absolute maximum ratings

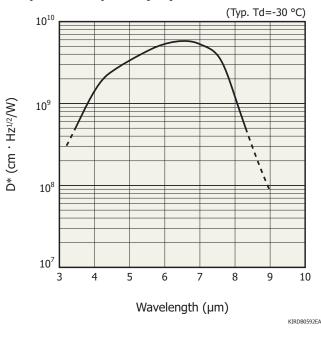
Parameter	Symbol	Value	Unit
Thermistor power dissipation	Pd_th	0.2	mW
TE-cooler allowable current	ITE max.	1	Α
Reverse voltage	VR	0.1	V
Operating temperature	Topr	-40 to +60	°C
Storage temperature	Tsta	-55 to +60	°C

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

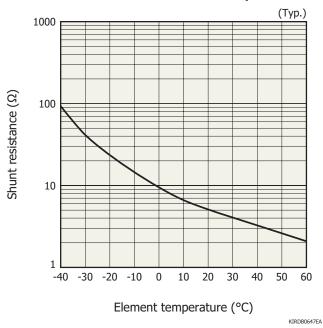
■ Electrical and optical characteristics (Td=-30 °C)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Peak sensitivity wavelength	λр		-	6.7	-	μm
Cutoff wavelength	λс		8.2	8.3	-	μm
Photosensitivity	S	λ=λρ	0.8	1.2	-	A/W
Shunt resistance	Rsh	VR=10 mV	13	40	-	Ω
Detectivity	D*	(λρ, 1200, 1)	4.0×10^{9}	6.0×10^{9}	-	cm·Hz ^{1/2} /W
Noise equivalent power	NEP	λ=λρ	-	1.5×10^{-11}	2.3×10^{-11}	W/Hz ^{1/2}
Rise time	tr	VR=0 V, RL=50 Ω 0 to 63%	-	-	10	ns

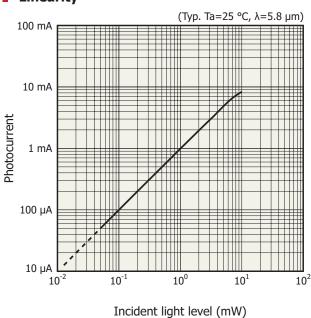
Spectral response (D*)



Shunt resistance vs. element temperature



Linearity

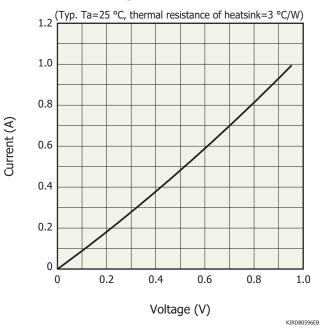


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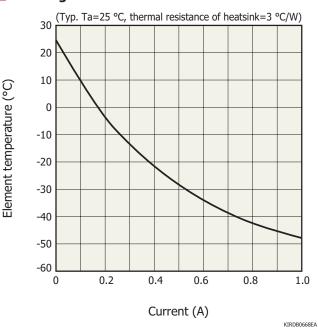
■ Specifications of two-stage TE-cooler (Ta=25 °C)

Parameter	Symbol	Min.	Тур.	Max.	Unit
TE cooler allowable current	ITE max.	-	-	1.0	Α
TE cooler allowable voltage	VTE max.	-	-	0.95	V
Thermistor resistance	Rth	8.1	9.0	9.9	kΩ
Thermistor power dissipation	Pd_th	-	-	0.2	mW

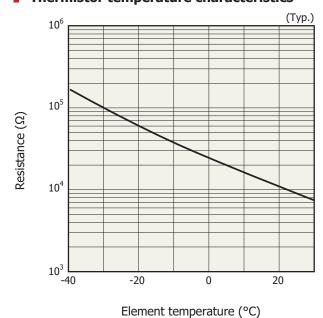
- Current vs. voltage characteristics of TE-cooler



- Cooling characteristics of TE-cooler

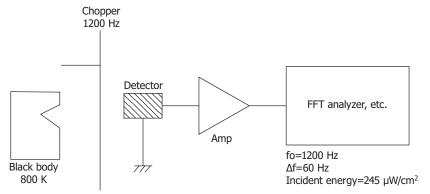


Thermistor temperature characteristics



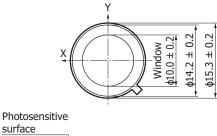
KIRDB0116EA

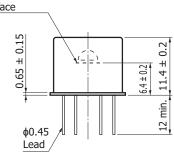
Measurement circuit example

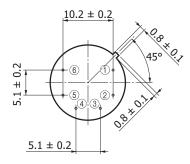


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► Dimensional outline (unit: mm)







- ① Detector (anode) ② Detector (cathode)
- ③TE-cooler (-)
- 4 TE-cooler (+)
- 56 Thermistor

KIRDA0242EA

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Related information

www.hamamatsu.com/sp/ssd/doc_en.html

- Precautions
 - Notice
 - · Metal, ceramic, plastic products
- Technical information
- · Infrared detector / Technical information

Information described in this material is current as of August 2018.

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